



《风光欣》技术资料

C2785

NPN SILICON TRANSISTOR

The 2SC2785 is designed for use in driver stage of A amplifier and low speed switching.

High Voltage $V_{CEO}: 50V$ MIN

Excellent hFE Linearity

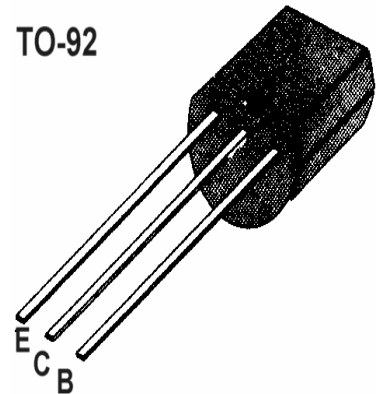
$h_{FE1}(0.1mA) / h_{FE2}(1.0mA)$

*Complementary to the 2SA1175 PNP Transistor.

ABSOLUTE MAXIMUM RATINGS($T_A=25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter -Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA
Base-Current	I_B	20	mA
Collector Dissipation	P_C	250	mW
Junction Temperature	T_J	150	
Storage Temperature	T_{STG}	-55 ~ +150	

TO-92



ELECTRICAL CHARACTERISTICS($T_A=25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
DC Current Gain	h_{FE}	$V_{CE}= 6V, I_C=0.1mA,$	50	185		
DC Current Gain	h_{FE}	$V_{CE}= 6V, I_C=1mA,$	110	200	600	
Noise Figure	NF	$V_{CE}= 6V, I_C= 0.1mA$		0.8	15	dB
		$f=1KHZ, R_G=2.0K$				
Current Gain -Bandwidth product	f_T	$V_{CE}= 6V, I_E= -10mA$	150	250	450	MHZ
Collector to Base capacitance	C_{OB}	$V_{CB}= 6V, I_E= 0, f=1MHZ$		3.0	4.0	pF
Collector Cut-off Current	I_{CBO}	$V_{CB}= 60V, I_E=0$			100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}= 5V, I_C=0,$			100	nA
Base-Emitter Voltage	V_{BE}	$V_{CE}= 6V, I_C= 1.0mA$	0.55	0.62	0.65	V
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C= 100mA, I_B=10A$		0.15	0.3	V
Base Saturation Voltage	$V_{BE(sat)}$	$I_C= 100mA, I_B=10A$		0.86	1.0	V

h_{FE2} CLASSIFICATION

Classification	RF	JF	HF	FF	EF	KF
HFE	110-180	135-220	170-270	200-320	250-400	300-600